Description

The MMSF10N03ZR2 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

 $V_{DS} = 30V I_{D} = 15A$

 $R_{DS(ON)} < 10m\Omega$ @ $V_{GS}=10V$

Application

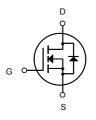
Battery protection

Load switch

Uninterruptible power supply



SOP-8 (SO-8)



N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
MMSF10N03ZR2	SOP-8(SO-8)	HXY MOSFET	3000

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units	
V _D S	Drain-Source Voltage	30	V	
Vgs	Gate-Source Voltage	±20	V	
ID@T _A =25°C	Continuous Drain Current ¹	15	А	
ID@Ta=70°C	Continuous Drain Current ¹	8	А	
Ірм	Pulsed Drain Current ²	45	А	
EAS	Single Pulse Avalanche Energy ³	12	mJ	
P _D @T _A =25°C	Total Power Dissipation ⁴	15	W	
Тѕтс	Storage Temperature Range	-55 to 150	°C	
TJ	Operating Junction Temperature Range	-55 to 150	°C	
_	Thermal Resistance Junction-ambient¹(t≤10s)	85	°C/W	
Reja	Thermal Resistance Junction-ambient ¹	25	°C/W	



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	30			V	
$\triangle BV_{DSS}/\triangle T_{J}$	BVDSS Temperature Coefficient	Reference to 25°C , I _D =1mA		0.034		V/°C	
В	Static Drain-Source On-Resistance ²	V_{GS} =10V , I_D =7A		8	10	mΩ	
R _{DS(ON)}	Static Dialii-Source Off-Nesistance	V _{GS} =4.5V , I _D =4A		12	15		
$V_{GS(th)}$	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.2	1.4	2.5	V	
$\triangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	VGS-VDS , ID -250UA	-	-3.84		mV/°C	
I _{DSS}	Drain-Source Leakage Current	V _{DS} =24V , V _{GS} =0V , T _J =25°C	-		1	- uA	
IDSS		V_{DS} =24V , V_{GS} =0V , T_J =55 $^{\circ}$ C	1		5	uA	
Igss	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	-		±100	nA	
gfs	Forward Transconductance	V _{DS} =5V , I _D =7A		6.2		S	
R_g	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz		1.04	2.1	Ω	
Qg	Total Gate Charge (4.5V)			6	8.4		
Q _{gs}	Gate-Source Charge	V_{DS} =15V , V_{GS} =4.5V , I_{D} =7A		2.2	3.1	nC	
Q_{gd}	Gate-Drain Charge			2	2.8		
T _{d(on)}	Turn-On Delay Time			1.2	2.4		
Tr	Rise Time	V_{DD} =15V , V_{GS} =10V , R_{G} =3.3 Ω		40	72.0	ns	
T _{d(off)}	Turn-Off Delay Time	I _D =7A		18	36.0		
T _f	Fall Time			7.2	14.4		
Ciss	Input Capacitance			983	1616		
Coss	Output Capacitance	V _{DS} =15V , V _{GS} =0V , f=1MHz		147	207.8	pF	
C _{rss}	Reverse Transfer Capacitance			109	162.6		
Is	Continuous Source Current ^{1,5}	\\-=\\-=0\\ Force Current			15	Α	
Ism	Pulsed Source Current ^{2,5}	V _G =V _D =0V , Force Current	-		35	Α	
V_{SD}	Diode Forward Voltage ²	V_{GS} =0 V , I_{S} =1 A , T_{J} =25 $^{\circ}$ C			1.2	V	
t _{rr}	Reverse Recovery Time		-	7.2		nS	
Qrr	Reverse Recovery Charge	IF=7A , dI/dt=100A/µs , T _J =25°C		2.9		nC	

Note:

- 1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width \leq 300us , duty cycle \leq 2%
- 3. The EAS data shows Max. rating . The test condition is V_{DD} =25V, V_{GS} =10V, L=0.1mH, I_{AS} =20A
- 4. The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.



Typical Characteristics

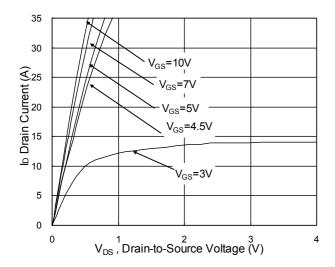


Fig.1 Typical Output Characteristics

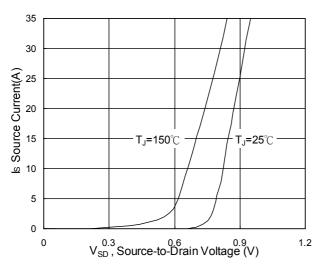


Fig.3 Forward Characteristics Of Reverse

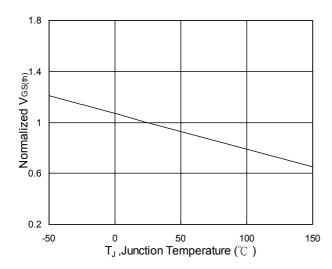


Fig.5 Normalized V_{GS(th)} vs. T_J

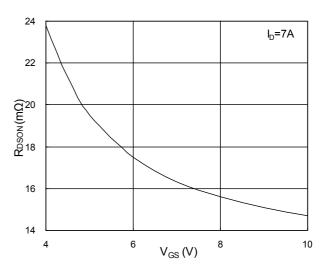


Fig.2 On-Resistance vs. Gate-Source

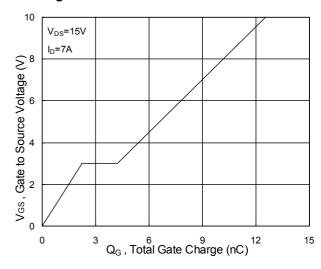


Fig.4 Gate-Charge Characteristics

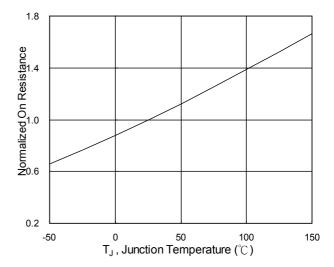
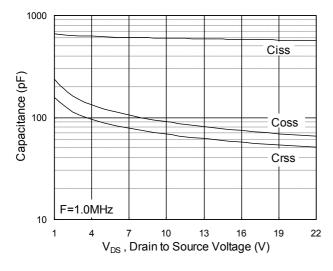


Fig.6 Normalized R_{DSON} vs. T_J



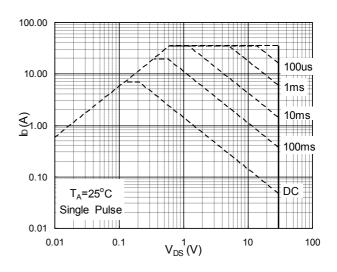


Fig.7 Capacitance

Fig.8 Safe Operating Area

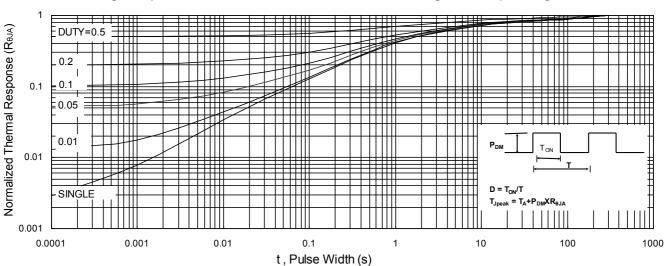


Fig.9 Normalized Maximum Transient Thermal Impedance

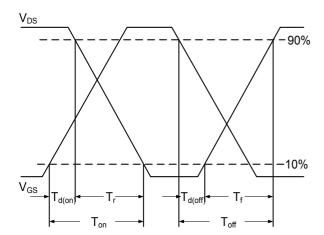


Fig.10 Switching Time Waveform

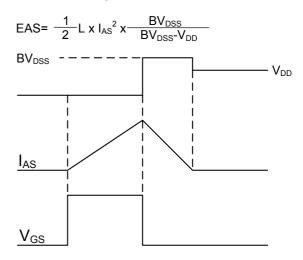
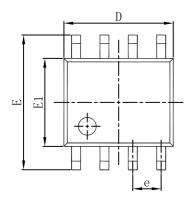
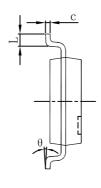
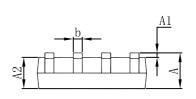


Fig.11 Unclamped Inductive Switching Waveform

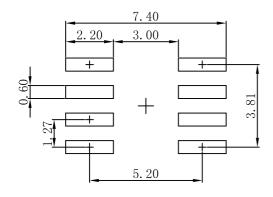
SOP-8(SO-8) Package Outline Dimensions







Symbol	Dimensions In Millimeters		Dimensions In Inches			
	Min	Max	Min	Max		
A	1. 350	1.750	0.053	0.069		
A1	0.100	0. 250	0.004	0.010		
A2	1.350	1.550	0.053	0.061		
b	0.330	0.510	0.013	0.020		
c	0.170	0.250	0.007	0.010		
D	4.800	5.000	0.189	0. 197		
e	1. 270 (1.270 (BSC)		0.050 (BSC)		
E	5.800	6.200	0. 228	0. 244		
E1	3.800	4.000	0.150	0. 157		
L	0.400	1.270	0.016	0.050		
θ	0°	8°	0°	8°		



- Note:
 1.Controlling dimension: in millimeters.
- 2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.

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